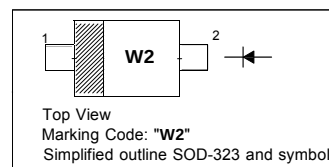


Silicon Epitaxial Planar Switching Diode

MARKING:W2

PINNING

PIN	DESCRIPTION
1	Cathode
2	Anode



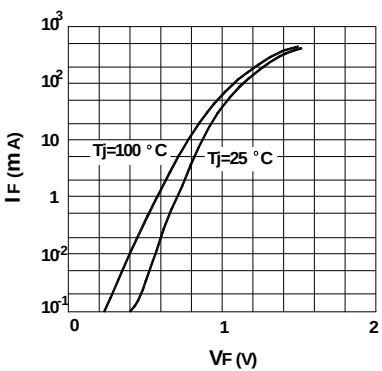
Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Repetitive Reverse Voltage	V_{RRM}	100	V
Average Rectified Forward Current	$I_{F(AV)}$	200	mA
Non-repetitive Peak Forward Surge Current at $t = 1\text{ s}$ at $t = 1\text{ }\mu\text{s}$	I_{FSM}	0.5 1	A
Power Dissipation	P_{tot}	200	mW
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	625	$^\circ\text{C/W}$
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	- 55 to + 150	$^\circ\text{C}$

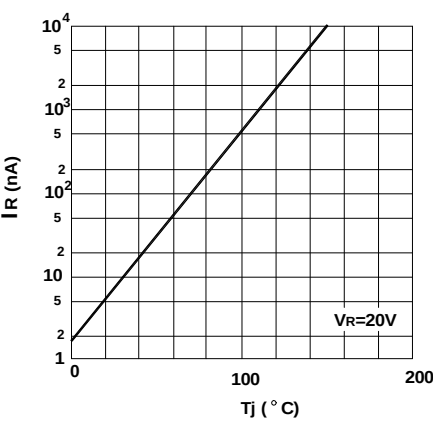
Electrical Characteristics ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Min.	Max.	Unit
Forward Voltage at $I_F = 10\text{ mA}$	V_F	-	1	V
Reverse Breakdown Voltage at $I_R = 5\text{ }\mu\text{A}$ at $I_R = 100\text{ }\mu\text{A}$	$V_{(BR)R}$ $V_{(BR)R}$	75 100	- -	V V
Reverse Current at $V_R = 20\text{ V}$ at $V_R = 75\text{ V}$ at $V_R = 20\text{ V}$, $T_J = 150^\circ\text{C}$	I_R	- - -	25 5 50	nA μA μA
Total Capacitance at $V_R = 0\text{ V}$, $f = 1\text{ MHz}$	C_{tot}	-	4	pF
Reverse Recovery Time at $I_F = I_R = 30\text{ mA}$, $R_L = 100\text{ }\Omega$, $I_{RR} = 3\text{ mA}$	t_{rr}	-	50	ns

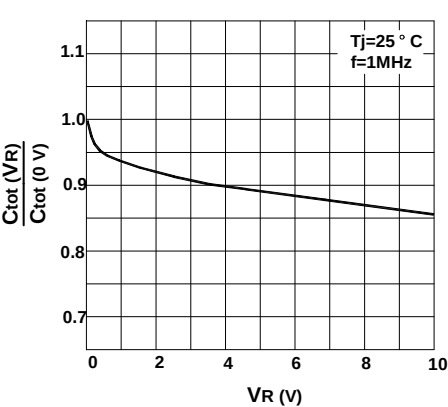
Forward characteristics



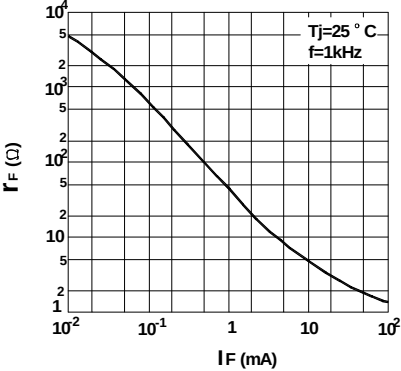
Leakage current vs. junction temperature



Reverse capacitance vs. reverse voltage



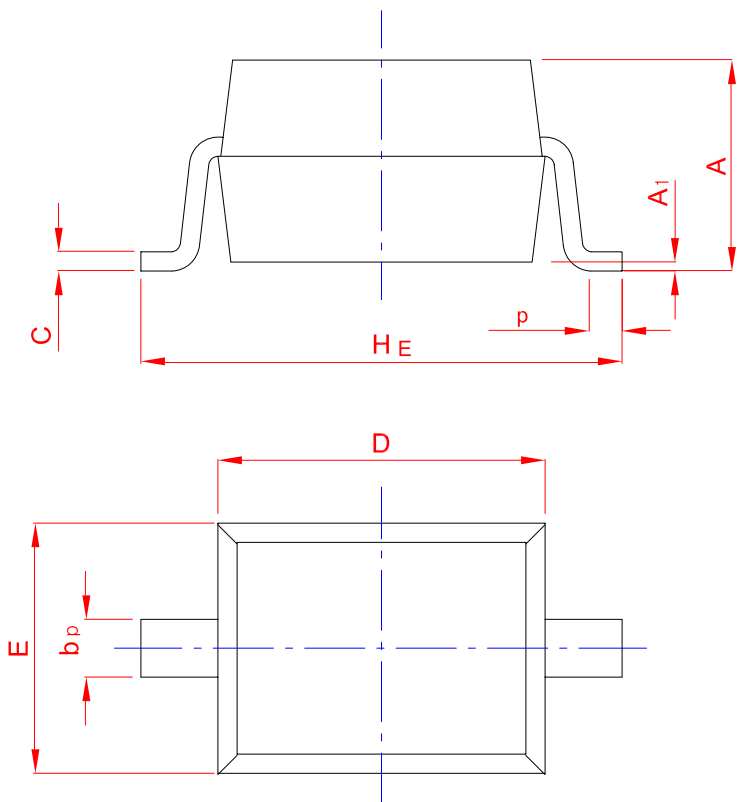
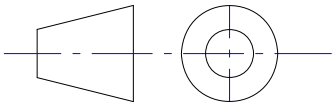
Dynamic forward resistance vs. forward current



PACKAGE OUTLINE

Plastic surface mounted package; 2 leads

SOD-323



UNIT	A	b _p	C	D	E	H _E	A ₁	L _p
mm	1.20 0.90	0.40 0.25	0.15 0.10	1.80 1.60	1.35 1.15	2.80 2.30	0.10 0.01	0.50 0.20